

N-channel TrenchMOS standard level FET 11 September 2012

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant •
- Repetitive avalanche rated •
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C •

1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control •
- Start-Stop micro-hybrid applications •
- Transmission control
- Ultra high performance power switching •

1.4 Quick reference data

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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|------|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 40 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> | [1] | - | - | 120 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 293 | W |
| Static char | acteristics | 1 | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | | - | 1.95 | 2.3 | mΩ |
| Dynamic cl | naracteristics | · | | | _ | | |
| Q_{GD} | gate-drain charge | V _{GS} = 10 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13; Fig. 14 | | - | 33.4 | - | nC |

[1] Continuous current is limited by package.

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2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------------|---|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | mb | D |
| 2 | D | drain | | |
| 3 | S | source | | G - C - C - C - C - C - C - C - C - C - |
| mb | D | mounting base; connected to drain | I 2 3 I 2PAK (SOT226) | mbb076 S |

3. Ordering information

| Table 3. Ordering information | | | | | | |
|-----------------------------------|---------|--|---------|--|--|--|
| Type number | Package | | | | | |
| | Name | Description | Version | | | |
| BUK7E2R3-40E | I2PAK | plastic single-ended package (I2PAK); TO-262 | SOT226 | | | |

4. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| BUK7E2R3-40E | BUK7E2R3-40E |

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 40 | V |
| V _{DGR} | drain-gate voltage | R _{GS} = 20 kΩ | | - | 40 | V |
| V _{GS} | gate-source voltage | T _j ≤ 175 °C; DC | | -20 | 20 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> | [1] | - | 120 | А |
| | | T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u> | [1] | - | 120 | А |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4 | | - | 1035 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | 293 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |

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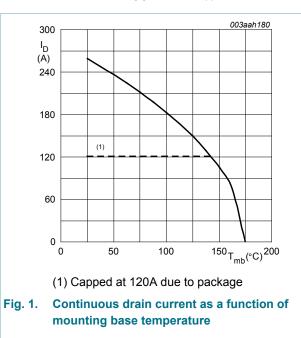
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| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|----------------------|---|---|--------|-----|------|------|
| Tj | junction temperature | | | -55 | 175 | °C |
| Source-drai | in diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | [1] | - | 120 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$ | | - | 1035 | А |
| Avalanche r | ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $\begin{split} I_D &= 120 \text{ A}; V_{sup} \leq 40 \text{V}; \text{R}_{GS} = 50 \Omega; \\ V_{GS} &= 10 \text{V}; \text{T}_{j(init)} = 25 ^{\circ}\text{C}; \text{unclamped}; \\ \hline \text{Fig. 3} \end{split}$ | [2][3] | - | 622 | mJ |

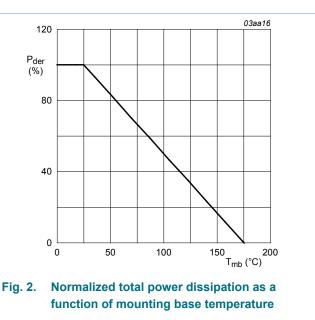
[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.



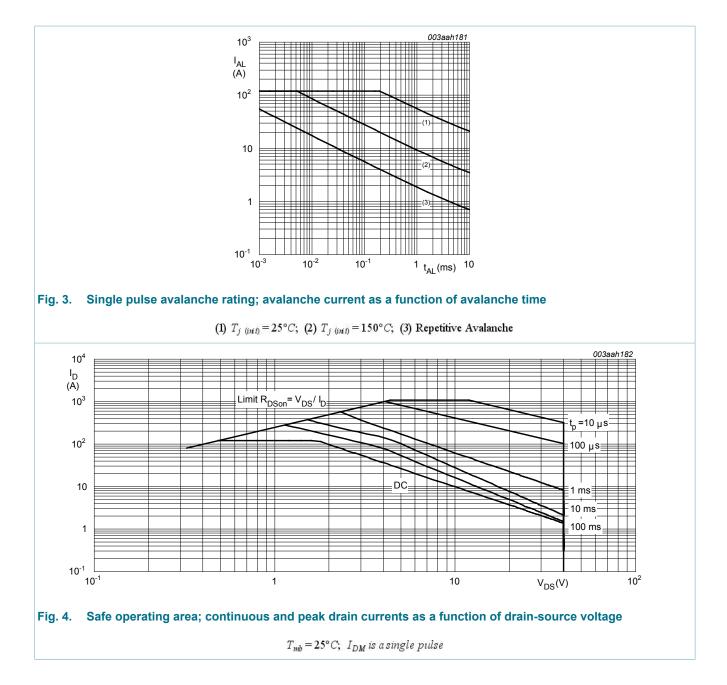
 $V_{GS} \ge 10V$



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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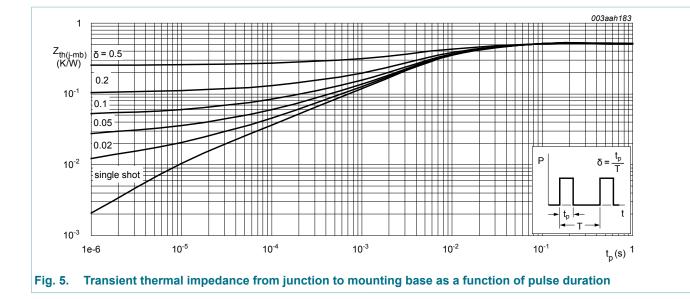


6. Thermal characteristics

| Fable 6. Thermal characteristics | | | | | | | |
|--------------------------------------|---|----------------------|--|-----|-----|------|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 5</u> | | - | - | 0.51 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | vetical in still air | | - | 65 | - | K/W |

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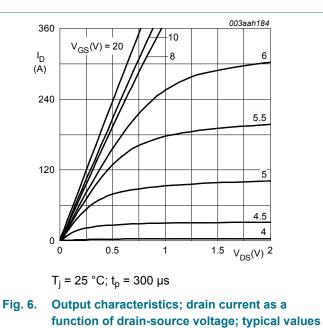


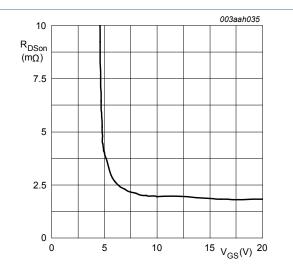
Characteristics 7.

| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
|----------------------|-------------------------------|--|-----|---|---|------|
| Static chara | acteristics | · · · · | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 40 | - | - | V |
| | breakdown voltage | I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C | 36 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10 | 2.4 | 3 | 4 | V |
| | - | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10 | - | - | 4.5 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10 | 1 | - | - | V |
| I _{DSS} | drain leakage current | V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.36 | 3 | μA |
| | | V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 0.36 3 μ - 500 μ 2 100 n | μA |
| I _{GSS} | gate leakage current | V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 4 V 4.5 V - V 3 μA 500 μA 100 nA 100 nA 2.3 mΩ 4.4 mΩ | nA |
| | | V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C | - | 36 - 36 - 2.4 3 4 - - 4.5 1 - - - 0.36 3 - 2 100 - 2 100 - 1.95 2.3 - - 4.4 | nA | |
| R _{DSon} | | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | - | 1.95 | 2.3 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11 | - | - | 4.4 | mΩ |
| Dynamic ch | naracteristics | · · · · | - I | - 1 | | |
| Q _{G(tot)} | total gate charge | I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; | - | 109.2 | - | nC |
| Q _{GS} | gate-source charge | Fig. 13; Fig. 14 | - | 27.5 | - | nC |
| Q _{GD} | gate-drain charge | | - | 33.4 | - | nC |

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| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
|---------------------|------------------------------|---|-------|------|------|------|
| C _{iss} | input capacitance | V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; | - | 6250 | 8500 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 15</u> | - | 1210 | 1450 | pF |
| C _{rss} | reverse transfer capacitance | $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$ $\text{R}_{G(ext)} = 5 \Omega$ | - | 605 | 840 | pF |
| t _{d(on)} | turn-on delay time | | - | 29 | - | ns |
| t _r | rise time | | - | 36 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 79 | - | ns |
| t _f | fall time | | - | 46 | - | ns |
| L _D | internal drain inductance | from upper edge of drain mounting base to center of die | - | 2.5 | - | nH |
| L _S | internal source inductance | from source lead to source bonding pad | - | 7.5 | - | nH |
| Source-dra | in diode | | | 1 | | |
| V _{SD} | source-drain voltage | I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u> | - | 0.8 | 1.2 | V |
| t _{rr} | reverse recovery time | I_{S} = 20 A; dI_{S}/dt = -100 A/µs; V _{GS} = 0 V; | - | 43 | - | ns |
| Q _r | recovered charge | V _{DS} = 25 V | - | 54 | - | nC |



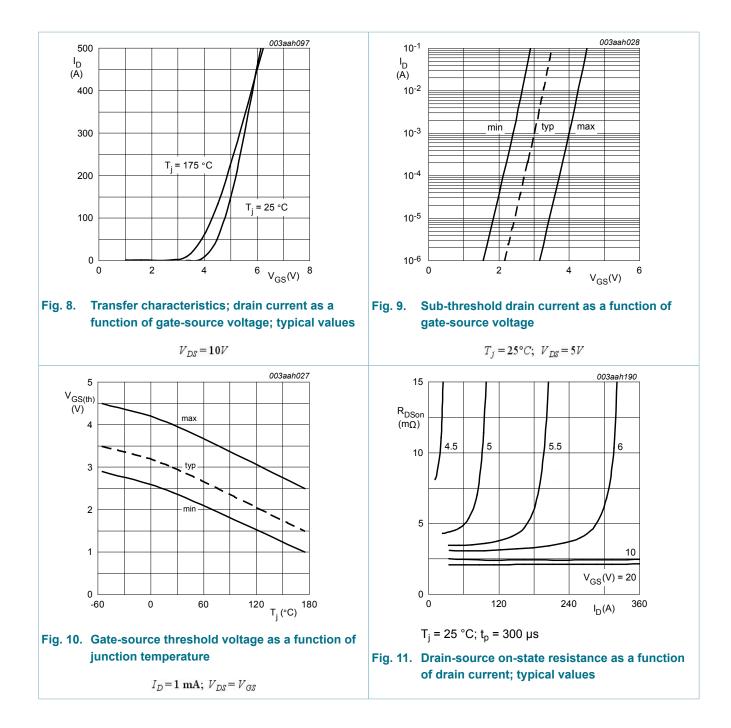




 $T_j = 25^{\circ}C; \ I_D = 25A$

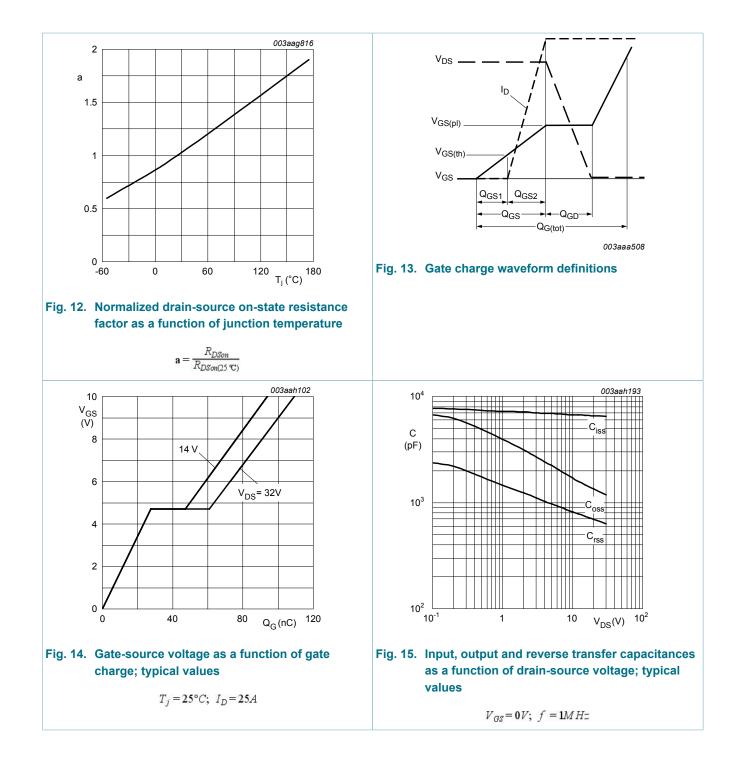
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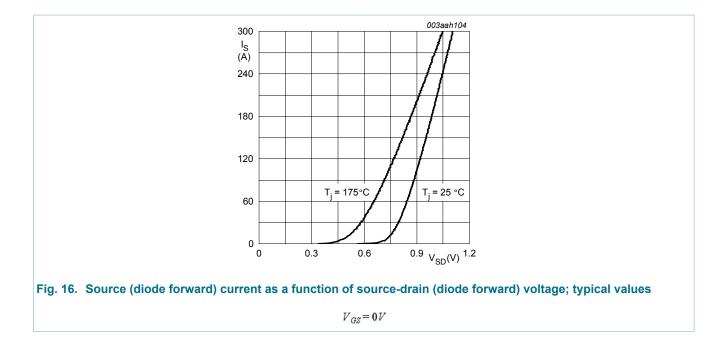
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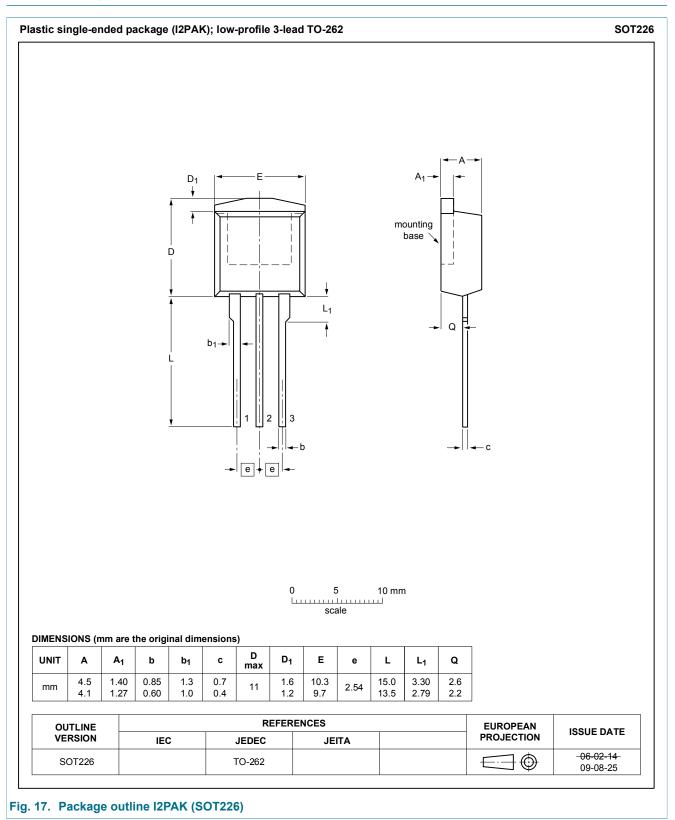
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8. Package outline



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9. Legal information

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| Document status [1][2] | Product status [<u>3]</u> | Definition |
|--------------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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